ABSTRACT

A new electrostatic discharge protection device is achieved. A p-well region is in a semiconductor substrate. An n+ region in the p-well region is connected to a first voltage supply. An n-well region in the p-well region is spaced from the n+ region such that a depletion region will extend therebetween during normal operation. A p+ region in the n-well region is connected to a second voltage supply of greater value than the first voltage supply during normal operation. Current is conducted through the n+ region to the p+ region during an electrostatic discharge event.